

Silicon NPN Power Transistors

2SC4928

DESCRIPTION

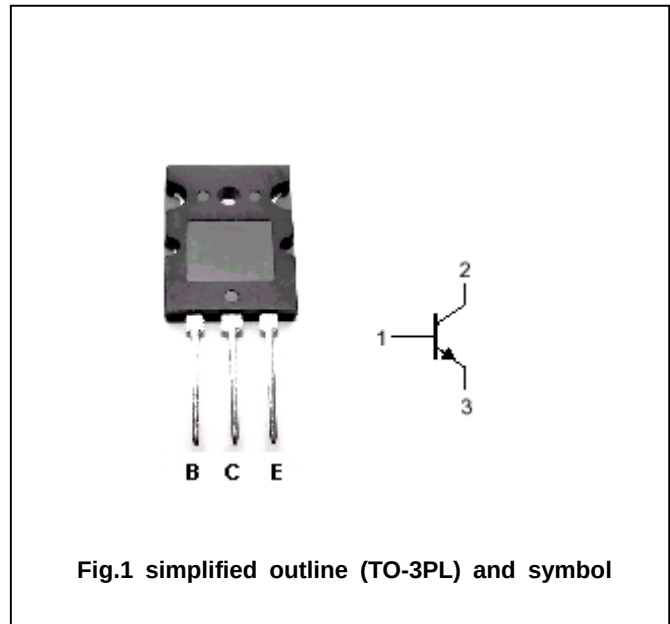
- With TO-3PL package
- High speed switching
- High breakdown voltage,high current

APPLICATIONS

- Character display horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		15	A
$I_{C(surge)}$	Collector surge current		20	A
P_C	Collector power dissipation	$T_C=25^{\circ}\text{C}$	150	W
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-55~150	$^{\circ}\text{C}$

Silicon NPN Power Transistors

2SC4928

CHARACTERISTICS

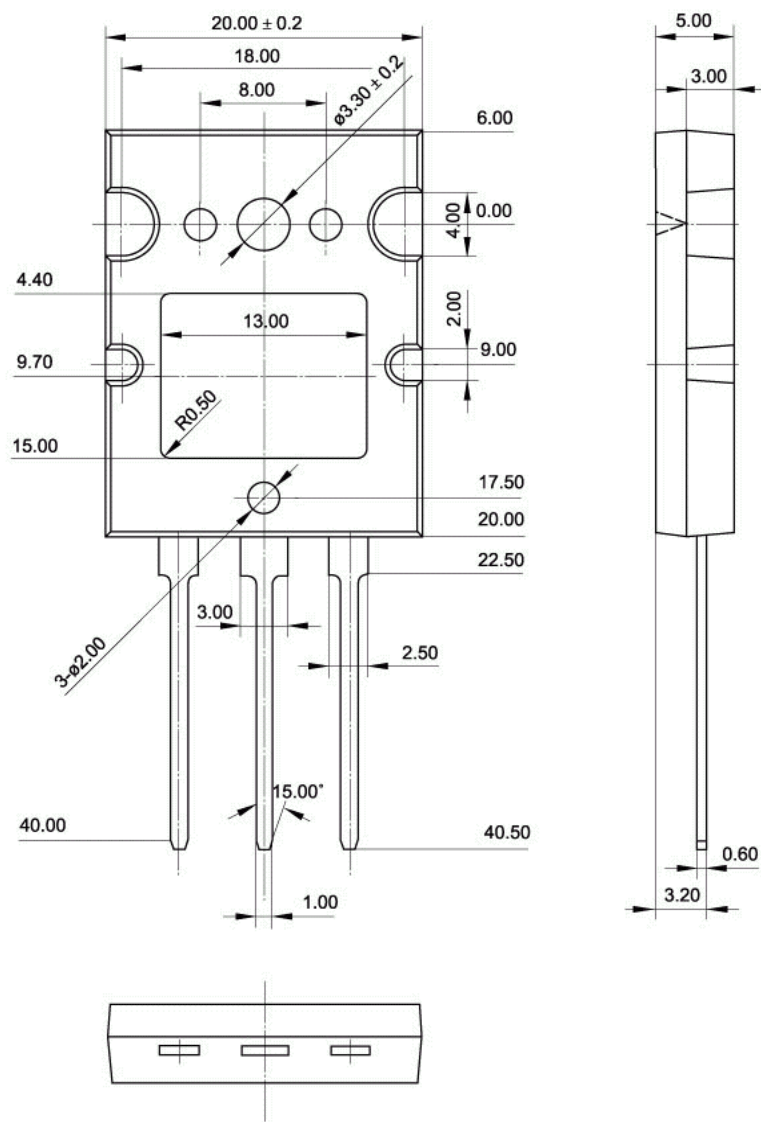
Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=10mA$; $R_{BE}=\infty$	800			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=10mA$; $I_C=0$	6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=12A$; $I_B=3A$			5.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=12A$; $I_B=3A$			1.5	V
I_{CES}	Collector cut-off current	$V_{CB}=1500V$; $R_{BE}=0$			500	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=6V$; $I_C=0$			500	μA
h_{FE}	DC current gain	$I_C=1A$; $V_{CE}=5V$			38	
t_f	Fall time	$I_C=8A$; $I_{B1}=1.4A$; $I_{B2}\approx -2.5A$ $f_H=31.5kHz$			0.5	μs

Silicon NPN Power Transistors

2SC4928

PACKAGE OUTLINE

Fig.2 Outline dimensions (unindicated tolerance: ± 0.50 mm)